

NSS60200L

60 V, 4.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

| Rating | Symbol | Max | Unit |
|--------------------------------|-----------|------|------|
| Collector-Emitter Voltage | V_{CEO} | -60 | Vdc |
| Collector-Base Voltage | V_{CBO} | -80 | Vdc |
| Emitter-Base Voltage | V_{EBO} | -7.0 | Vdc |
| Collector Current - Continuous | I_C | -2.0 | A |
| Collector Current - Peak | I_{CM} | -4.0 | A |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|--------------------------|----------------|---------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D (Note 1) | 460 | mW |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ (Note 1) | 270 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D (Note 2) | 540 | mW |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ (Note 2) | 230 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

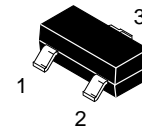
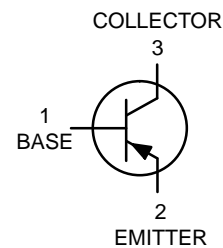
1. FR-4 @ 100 mm², 1 oz. copper traces.
2. FR-4 @ 500 mm², 1 oz. copper traces.



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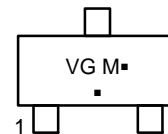
www.onsemi.com

**-60 VOLTS, 4.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 80 mΩ**



SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



VG = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|---------------------|------------------|
| NSS60200LT1G | SOT-23 (Pb-Free) | 3000/Tape & Reel |
| NSV60200LT1G | SOT-23 (Pb-Free) | 3000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSS60200L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|----------------------|------|---|------|------|
| Collector–Emitter Breakdown Voltage (I _C = –10 mAdc, I _B = 0) | V _{(BR)CEO} | –60 | – | – | Vdc |
| Collector–Base Breakdown Voltage (I _C = –0.1 mAdc, I _E = 0) | V _{(BR)CBO} | –80 | – | – | Vdc |
| Emitter–Base Breakdown Voltage (I _E = –0.1 mAdc, I _C = 0) | V _{(BR)EBO} | –7.0 | – | – | Vdc |
| Collector Cutoff Current (V _{CB} = –60 Vdc, I _E = 0) | I _{CBO} | – | – | –0.1 | μAdc |
| Emitter Cutoff Current (V _{EB} = –6.0 Vdc) | I _{EBO} | – | – | –0.1 | μAdc |

ON CHARACTERISTICS

| | | | | | |
|---|----------------------|--------------------------|--------------------------------------|--------------------------------------|-----|
| DC Current Gain (Note 3) (I _C = –10 mA, V _{CE} = –2.0 V) (I _C = –500 mA, V _{CE} = –2.0 V) (I _C = –1.0 A, V _{CE} = –2.0 V) (I _C = –2.0 A, V _{CE} = –2.0 V) | h _{FE} | 150 150 100 100 | – 300 – – | – – – – | |
| Collector–Emitter Saturation Voltage (Note 3) (I _C = –0.1 A, I _B = –0.010 A) (I _C = –1.0 A, I _B = –0.100 A) (I _C = –1.0 A, I _B = –0.010 A) (I _C = –2.0 A, I _B = –0.200 A) | V _{CE(sat)} | – – – – | –0.017 –0.095 –0.180 –0.170 | –0.030 –0.120 –0.270 –0.220 | V |
| Base–Emitter Saturation Voltage (Note 3) (I _C = –1.0 A, I _B = –0.010 A) | V _{BE(sat)} | – | – | –0.900 | V |
| Base–Emitter Turn–on Voltage (Note 3) (I _C = –1.0 A, V _{CE} = –2.0 V) | V _{BE(on)} | – | – | –0.850 | V |
| Cutoff Frequency (I _C = –100 mA, V _{CE} = –5.0 V, f = 100 MHz) | f _T | 100 | – | – | MHz |
| Input Capacitance (V _{EB} = 0.5 V, f = 1.0 MHz) | C _{ibo} | – | – | 325 | pF |
| Output Capacitance (V _{CB} = 3.0 V, f = 1.0 MHz) | C _{obo} | – | – | 62 | pF |

SWITCHING CHARACTERISTICS

| | | | | | |
|---|----------------|---|---|-----|----|
| Delay (V _{CC} = –30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _d | – | – | 60 | ns |
| Rise (V _{CC} = –30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _r | – | – | 120 | ns |
| Storage (V _{CC} = –30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _s | – | – | 400 | ns |
| Fall (V _{CC} = –30 V, I _C = 750 mA, I _{B1} = 15 mA) | t _f | – | – | 130 | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

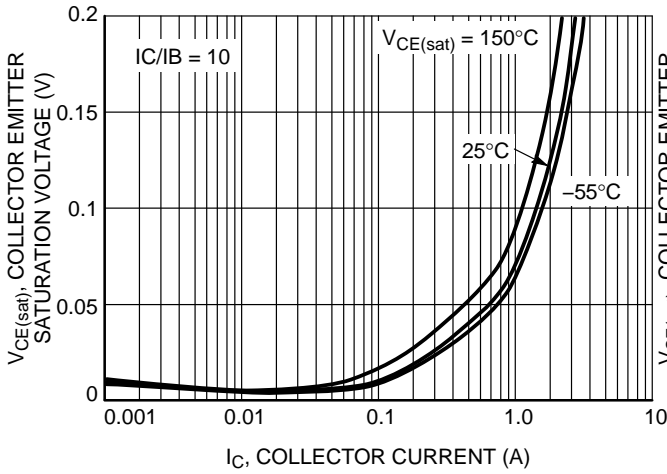


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

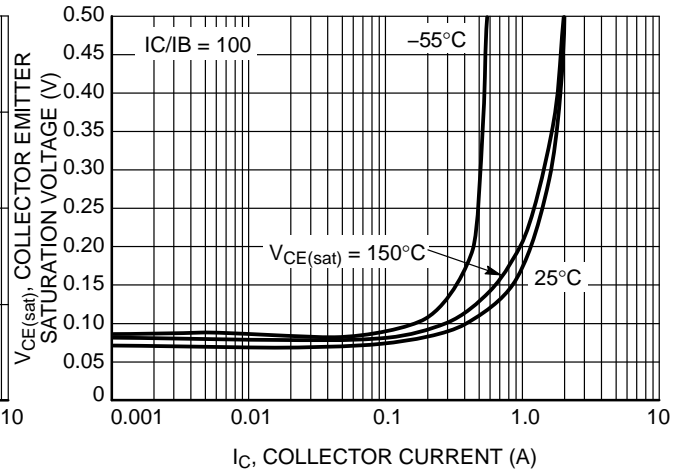


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

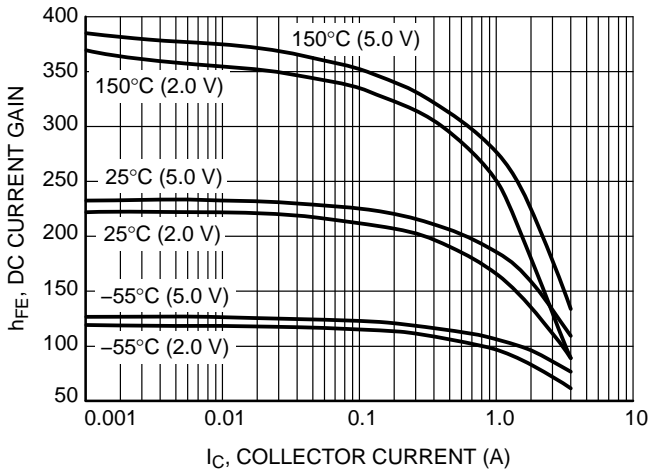


Figure 3. DC Current Gain vs. Collector Current

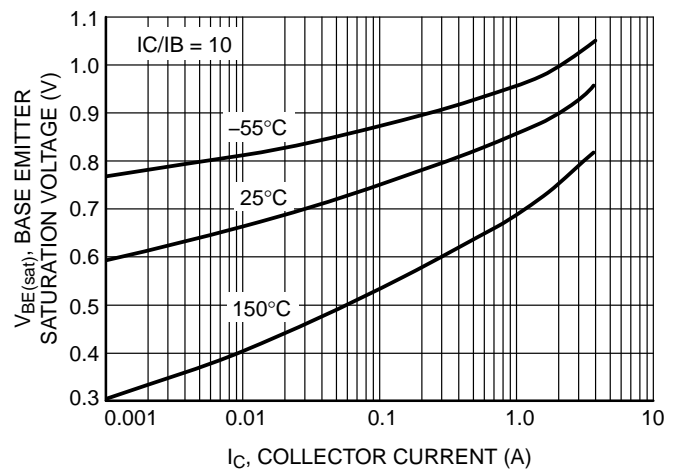


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

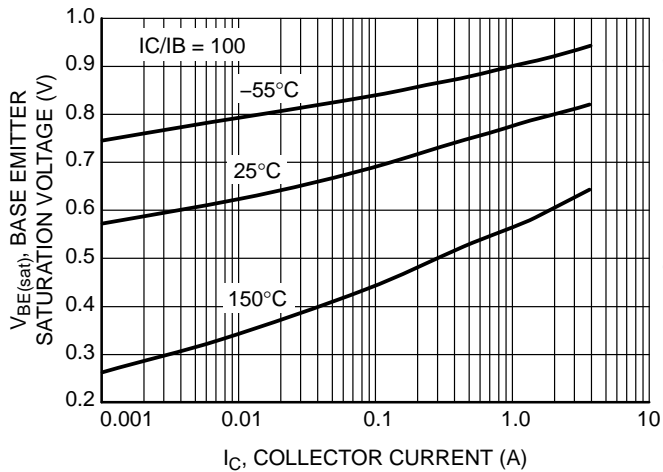


Figure 5. Base Emitter Saturation Voltage vs. Collector Current

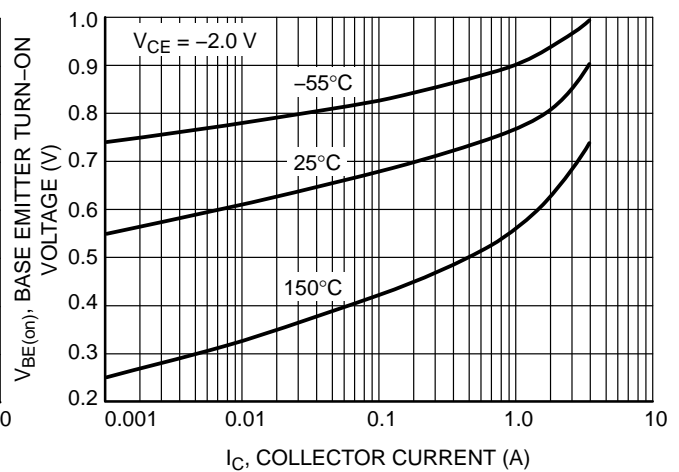


Figure 6. Base Emitter Turn-On Voltage vs. Collector Current

TYPICAL CHARACTERISTICS

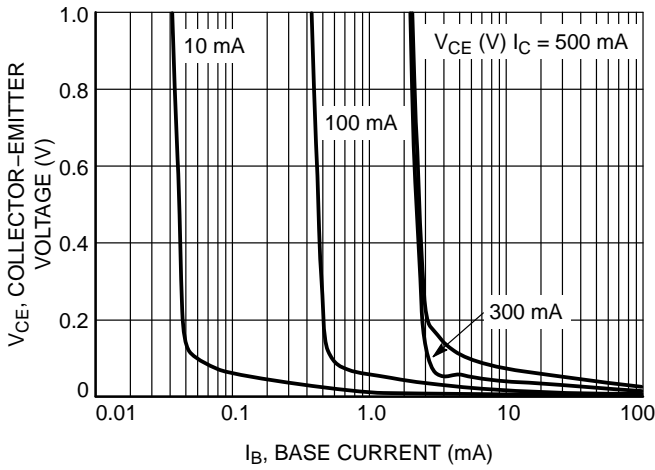


Figure 7. Saturation Region

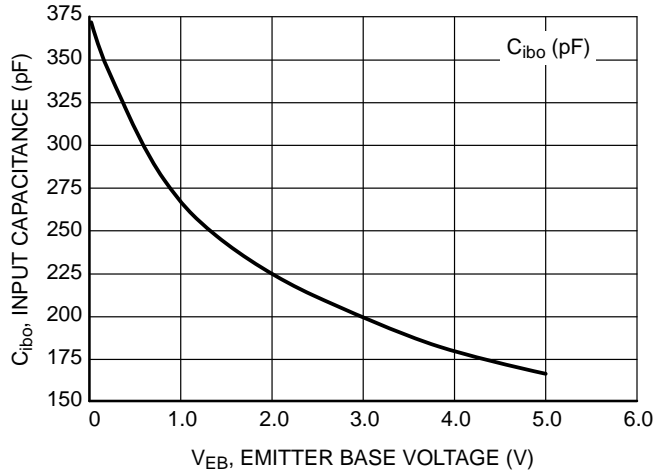


Figure 8. Input Capacitance

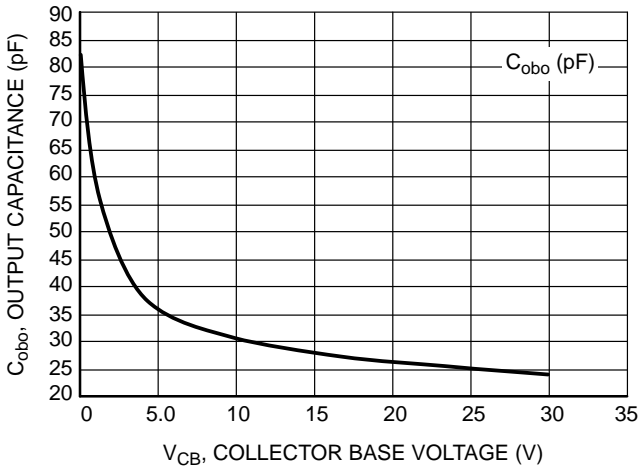


Figure 9. Output Capacitance

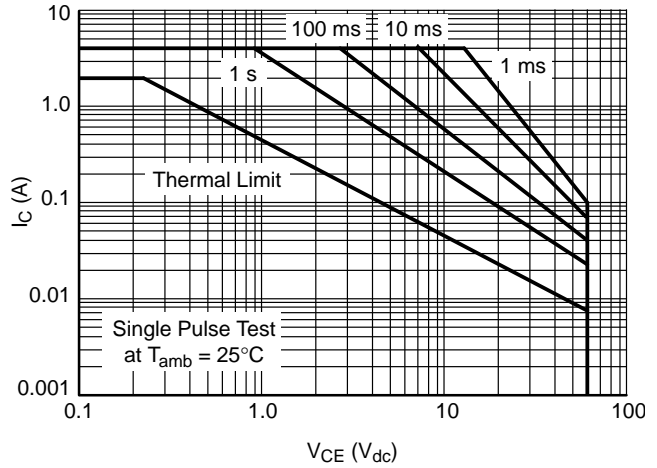


Figure 10. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

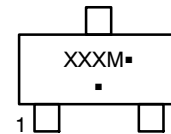
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | --- | 10° | 0° | --- | 10° |

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

| | | |
|-------------------------|------------------------|--|
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